

Single N-channel MOSFET

ELM58988WA-S

<http://www.elm-tech.com>

■ General description

ELM58988WA-S uses advanced trench technology to provide excellent $R_{ds(on)}$, low gate charge and low gate threshold voltage.

■ Features

- $V_{ds}=100V$
- $I_d=4.6A$
- $R_{ds(on)} = 130m\Omega$ ($V_{gs}=10V$)
- $R_{ds(on)} = 138m\Omega$ ($V_{gs}=4.5V$)

■ Maximum absolute ratings

$T_a=25^\circ C$. Unless otherwise noted.

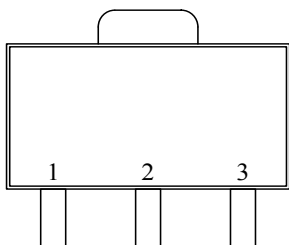
Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{ds}	100	V
Gate-source voltage	V_{gs}	± 20	V
Continuous drain current($T_j=150^\circ C$)	I_d	$T_a=25^\circ C$	4.6
		$T_a=70^\circ C$	3.6
Pulsed drain current	I_{dm}	10	A
Power dissipation	P_d	$T_c=25^\circ C$	1.45
		$T_c=70^\circ C$	0.60
Operating junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	- 55 to 150	$^\circ C$

■ Thermal characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal resistance junction-to-ambient	$R_{\theta ja}$		120	$^\circ C/W$

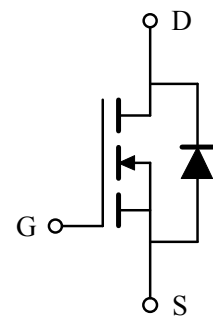
■ Pin configuration

SOT-89(TOP VIEW)



Pin No.	Pin name
1	GATE
2	DRAIN
3	SOURCE

■ Circuit



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■ Electrical characteristics

Ta=25°C. Unless otherwise noted.

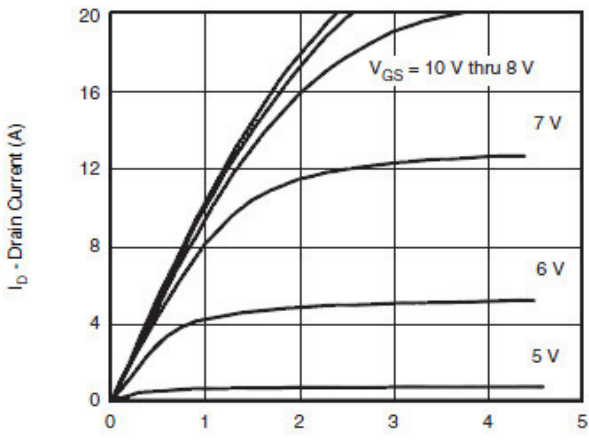
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	BVdss	Id=250μA, Vgs=0V	100			V
Zero gate voltage drain current	Idss	Vds=80V, Vgs=0V Ta=85°C			1	μA
					5	
Gate-body leakage current	Igss	Vds=0V, Vgs=±20V			±100	nA
Gate threshold voltage	Vgs(th)	Vds=Vgs, Id=250μA	0.5		2.5	V
On state drain current	Id(on)	Vgs=4.5V, Vds≥5V	10			A
Static drain-source on-resistance	Rds(on)	Vgs=10V, Id=4.8A		118	130	mΩ
		Vgs=4.5V, Id=3.6A		128	138	
Forward transconductance	Gfs	Vds=15V, Id=5.3A		24		S
Diode forward voltage	Vsd	Is=2.0A, Vgs=0V		0.8	1.2	V
Max. body-diode continuous current	Is				1.6	A
DYNAMIC PARAMETERS						
Input capacitance	Ciss	Vgs=0V, Vds=50V, f=1MHz		600		pF
Output capacitance	Coss			90		pF
Reverse transfer capacitance	Crss			60		pF
SWITCHING PARAMETERS						
Total gate charge	Qg	Vgs=5V, Vds=50V Id≐3A		12.0	18.0	nC
Gate-source charge	Qgs			4.2		nC
Gate-drain charge	Qgd			5.2		nC
Turn-on delay time	td(on)	Vgs=10V, Vds=50V RL=12.5Ω, Id≐3.0A Rgen=1.0Ω		15	25	ns
Turn-on rise time	tr			15	25	ns
Turn-off delay time	td(off)			20	30	ns
Turn-off fall time	tf			15	25	ns

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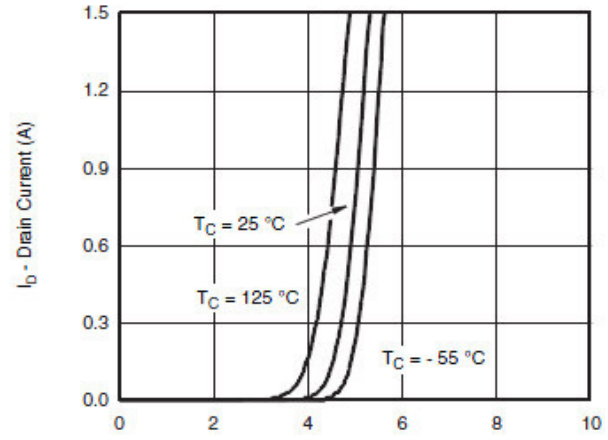
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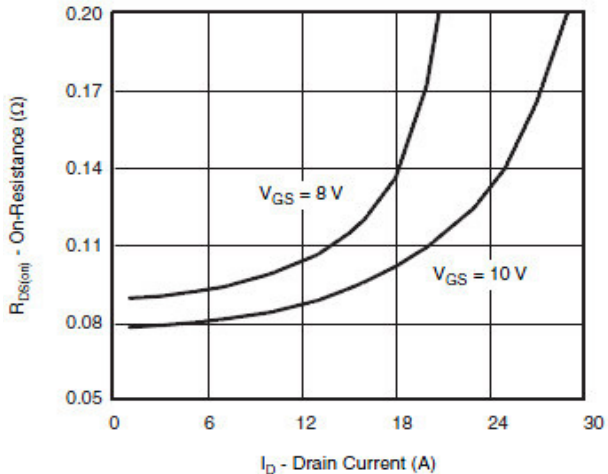
Typical electrical and thermal characteristics



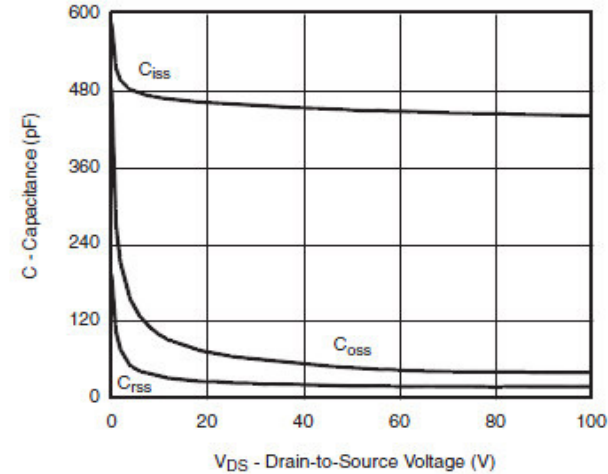
Output Characteristics



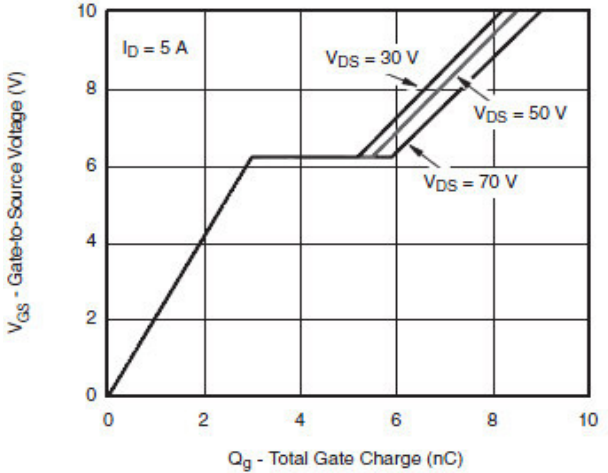
Transfer Characteristics



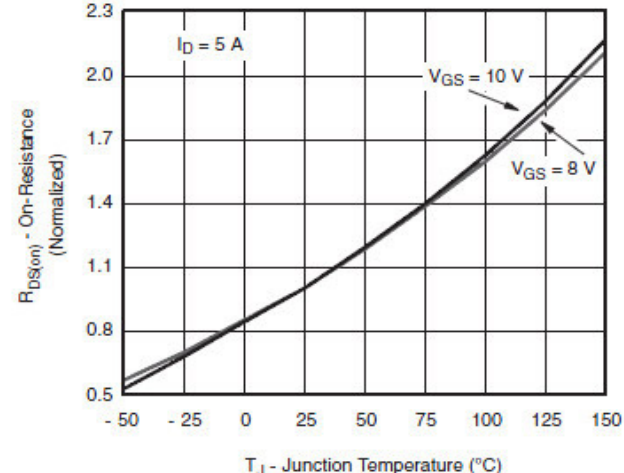
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



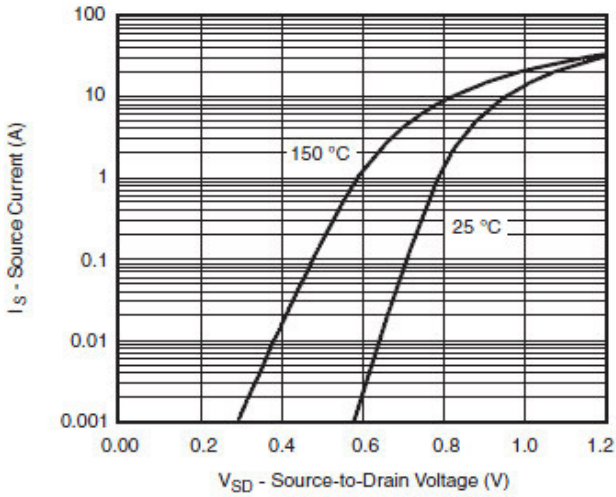
On-Resistance vs. Junction Temperature



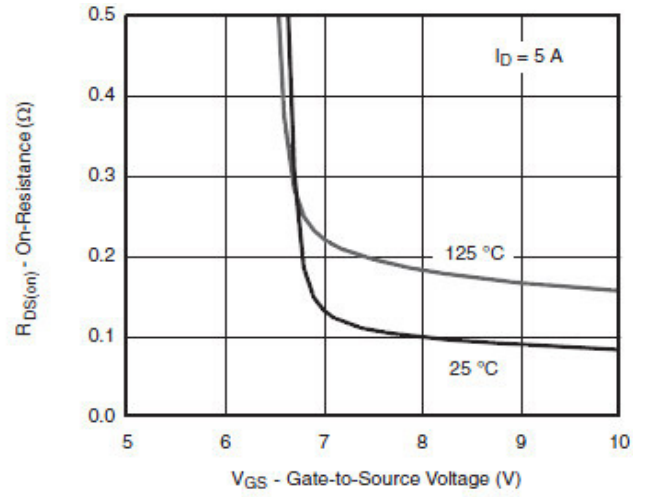
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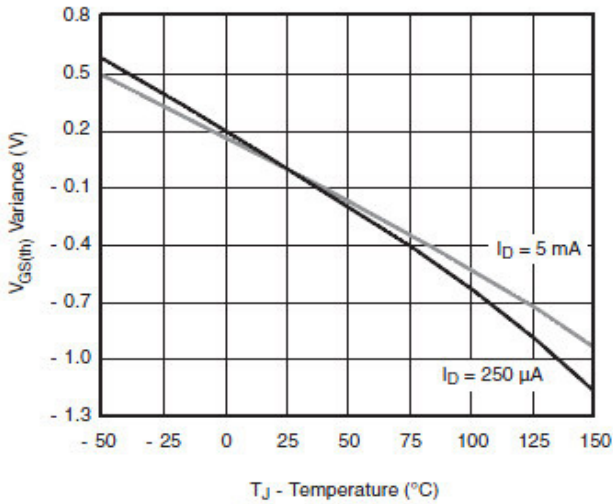
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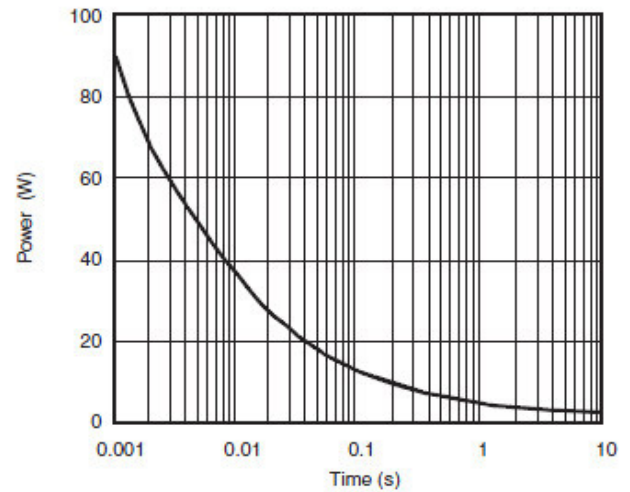
Source-Drain Diode Forward Voltage



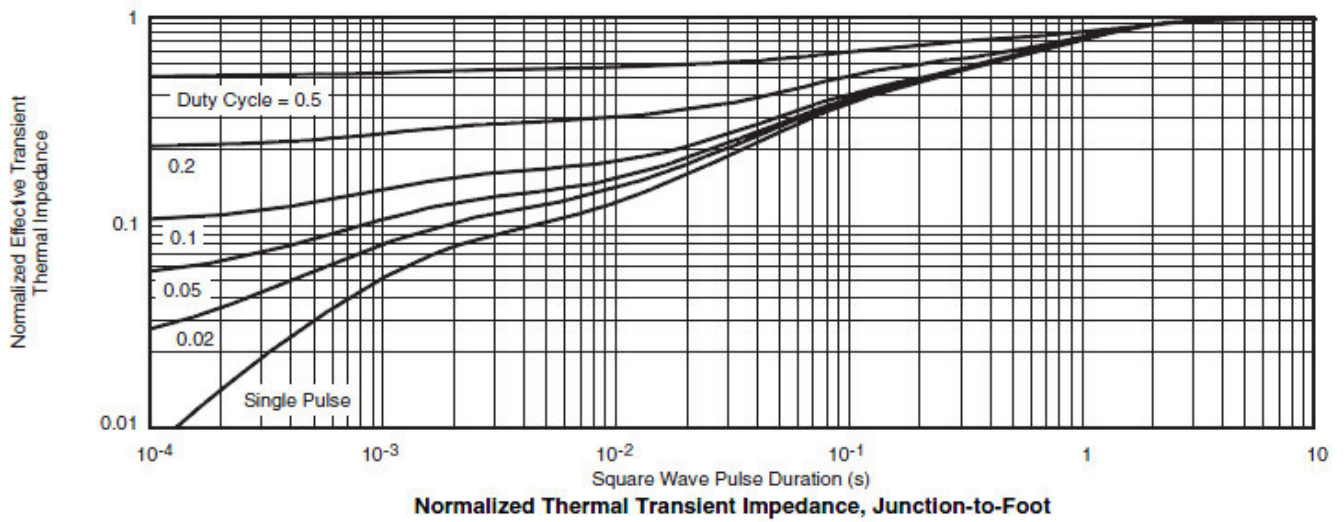
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

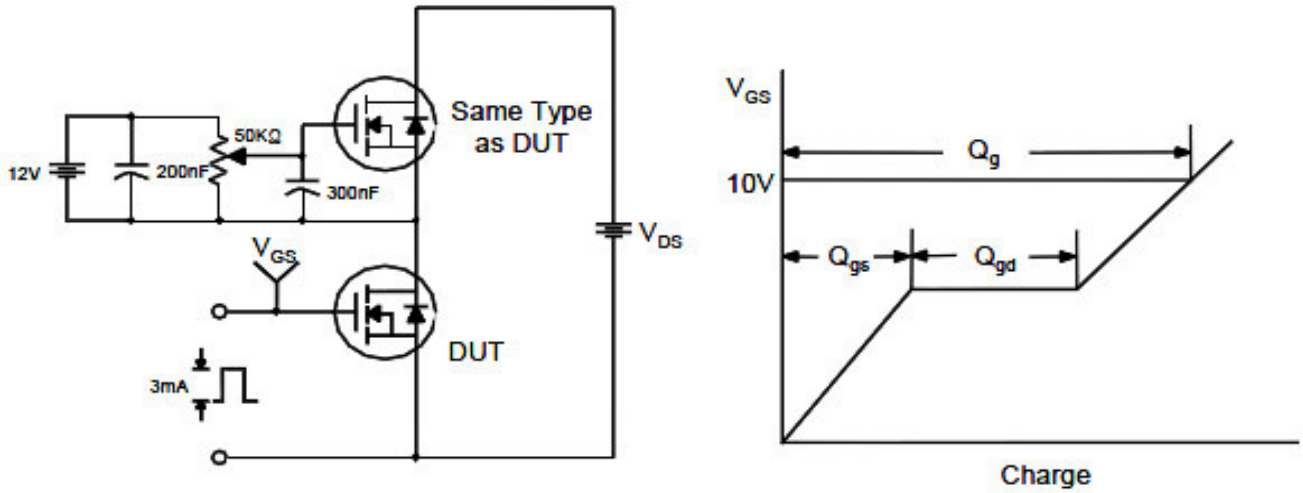
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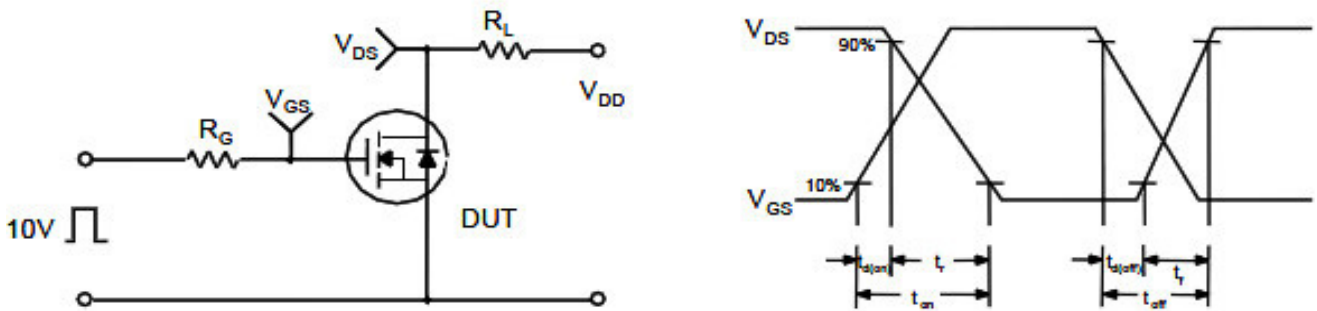
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■ Test circuit and waveform

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

